

isc Silicon NPN Power Transistor

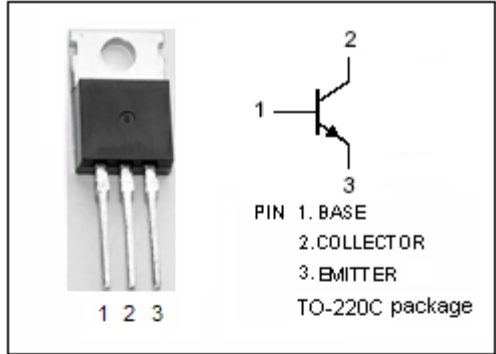
BDY80

DESCRIPTION

- Continuous Collector Current- $I_C= 4A$
- Collector Power Dissipation-
: $P_C= 36W @T_C= 25^\circ C$
- Complement to Type BDY82

APPLICATIONS

- Designed for general purpose switching and amplifier applications.

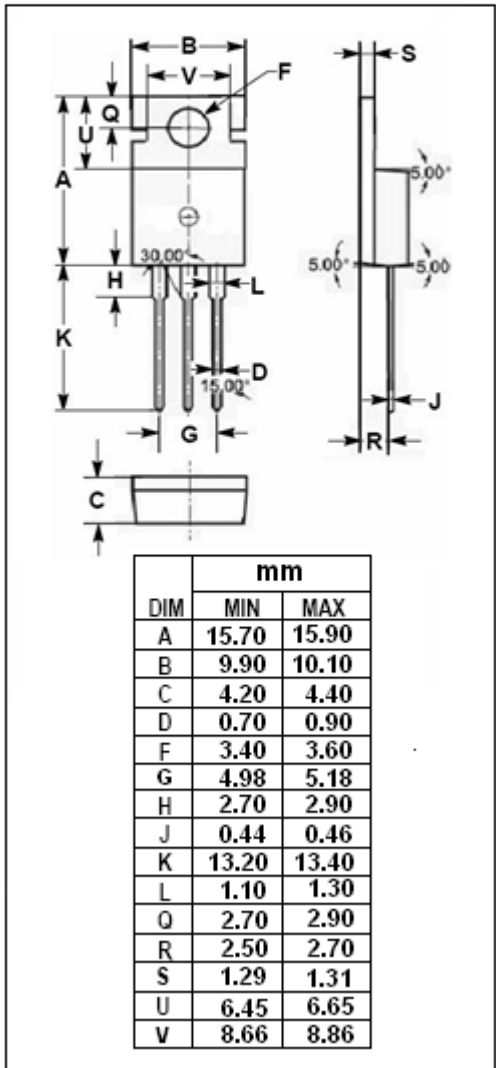


ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	40	V
V_{CEX}	Collector-Emitter Voltage $V_{BE} = -1.5V$	40	V
V_{CEO}	Collector-Emitter Voltage	35	V
V_{EBO}	Emitter-Base Voltage	10	V
I_C	Collector Current-Continuous	4	A
I_B	Base Current-Continuous	2	A
P_C	Collector Power Dissipation @ $T_C=25^\circ C$	36	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55~175	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	3.5	$^\circ C/W$



isc Silicon NPN Power Transistor**BDY80****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=100\text{mA}; I_B=0$	35			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=10\text{mA}; I_E=0$	40			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=10\text{mA}; I_C=0$	10			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=1\text{A}; I_B=0.05\text{A}$			1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=0.5\text{A}; V_{CE}=5\text{V}$			0.9	V
I_{CEO}	Collector Cutoff Current	$V_{CE}=20\text{V}; I_B=0$			10	mA
I_{CBO}	Collector Cutoff Current	$V_{CB}=20\text{V}; I_E=0$			0.2	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			0.1	mA
h_{FE-1}	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=5\text{V}$	40		240	
h_{FE-2}	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$	20			
f_T	Current Gain-Bandwidth Product	$I_C=0.5\text{A}; V_{CE}=10\text{V}$		1		MHz

◆ **h_{FE-1} Classifications**

A	B	C
40-80	70-140	120-240